



# N-Channel Reduced $Q_g$ , Fast Switching MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)				
30	0.0085 at V <sub>GS</sub> = 10 V	15				
30	0.0125 at V <sub>GS</sub> = 4.5 V	12				

# • Halogen-free According to IEC 61249-2-21 **Available**

**FEATURES** 

TrenchFET® Gen II Power MOSFETs

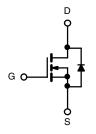
PWM Optimized

100 % R<sub>g</sub> Tested

# HALOGEN FREE Available

#### **APPLICATIONS**

- High-Side DC/DC Conversion
  - Notebook
  - Desktop
  - Server



N-Channel MOSFET

	SO-8		
S 1 S 2 S 3 G 4		8 7 6 5	D D D
	Top View		

Ordering Information: Si4384DY-T1-E3 (Lead (Pb)-free)

Si4384DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	T <sub>A</sub> = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	30		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
0 11 0 17 170 2013	T <sub>A</sub> = 25 °C	I <sub>D</sub>	15	10	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		12	8	
Pulsed Drain Current		I <sub>DM</sub>	± 50		Α
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2.8	1.3	
Single Pulse Avalanche Current		I <sub>AS</sub>	25		
Avalanche Energy	L = 0.1 mH	E <sub>AS</sub>	31		mJ
M	T <sub>A</sub> = 25 °C	В	3.1	1.47	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	P <sub>D</sub>	2	0.95	
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum lunction to Ambient (MOCFET)	t ≤ 10 s	R <sub>thJA</sub>	34	40	1	
Maximum Junction-to-Ambient (MOSFET) <sup>a</sup>	Steady State		71	85	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	17	20		

a. Surface Mounted on 1" x 1" FR4 board.

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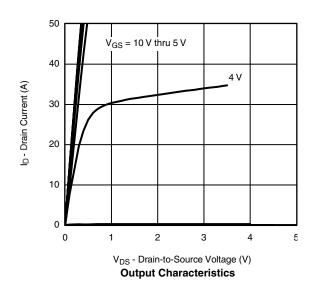
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3.0	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zana Cata Valtana Brain Comunit		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 70 °C		10	- μΑ		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
	Б	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 15 A	0.007 0.0085		0.0085	Ω	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 12 A		0.0105	0.0125		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 15 A		56		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 2.8 A, V <sub>GS</sub> = 0 V		0.75	1.1	V	
Dynamic <sup>b</sup>			1	•			
Total Gate Charge	$Q_g$			12	18		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 15 \text{ A}$		5.9		nC	
Gate-Drain Charge	$Q_{gd}$			4.0			
Gate Resistance	$R_{g}$		0.8	1.7	2.5	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			10	15		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		13	20		
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_\text{D}\cong\text{1 A, V}_\text{GEN}=\text{10 V, R}_\text{g}=\text{6}~\Omega$		45	70	ns	
Fall Time	t <sub>f</sub>			13	20		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.8 A, dI/dt = 100 A/μs		25	50		

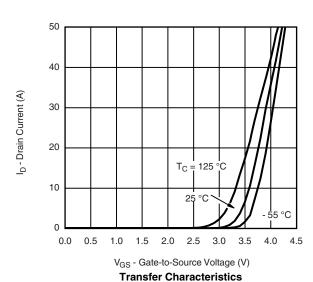
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



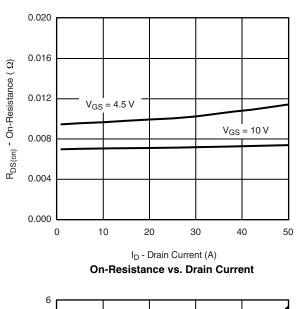


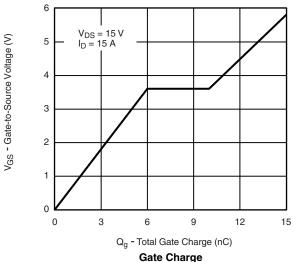


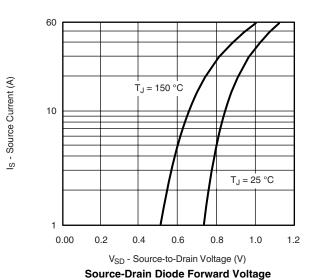


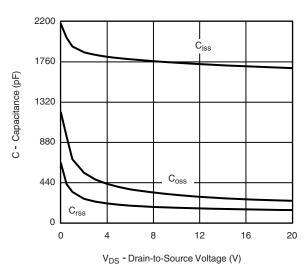


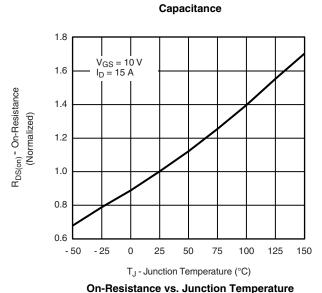
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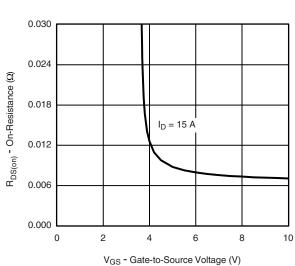










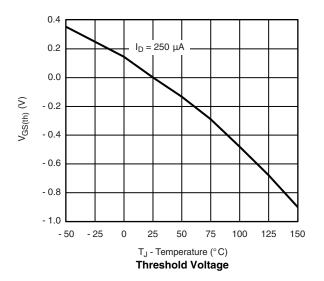


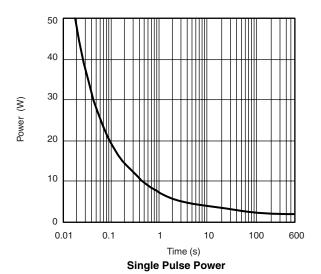
On-Resistance vs. Gate-to-Source Voltage

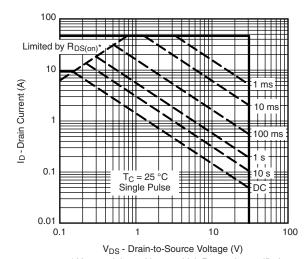
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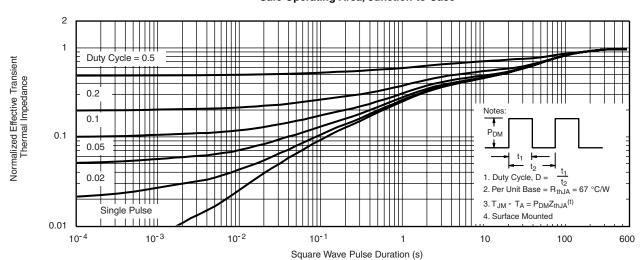
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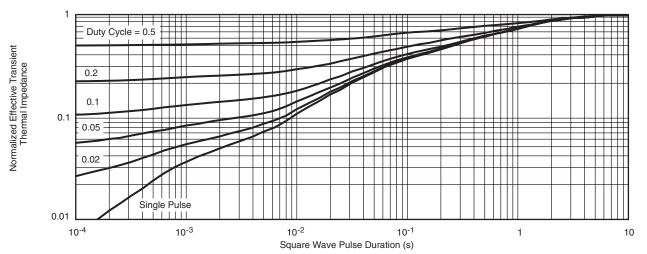
\* V<sub>GS</sub> > minimum V<sub>GS</sub> at which R<sub>DS(on)</sub> is specified **Safe Operating Area, Junction-to-Case** 



Normalized Thermal Transient Impedance, Junction-to-Ambient



#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?72645">www.vishay.com/ppg?72645</a>.



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A <sub>1</sub>	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I. 11-Sep-06						

DWG: 5498

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#### **RECOMMENDED MINIMUM PADS FOR SO-8**



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

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